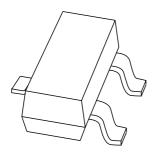
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBS3906 PNP general purpose transistor

Product specification Supersedes data of 1999 Apr 22 2004 Feb 02





PNP general purpose transistor

PMBS3906

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

 General purpose switching and amplification, e.g. telephony and professional communication equipment.

DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complement: PMBS3904.

MARKING

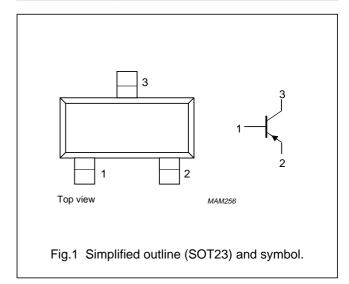
TYPE NUMBER	MARKING CODE(1)	
PMBS3906	*O6	

Note

* = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
PMBS3906	_	plastic surface mounted package; 3 leads SC	

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V _{CEO}	collector-emitter voltage	open base	_	-40	٧
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current capability		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

PNP general purpose transistor

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

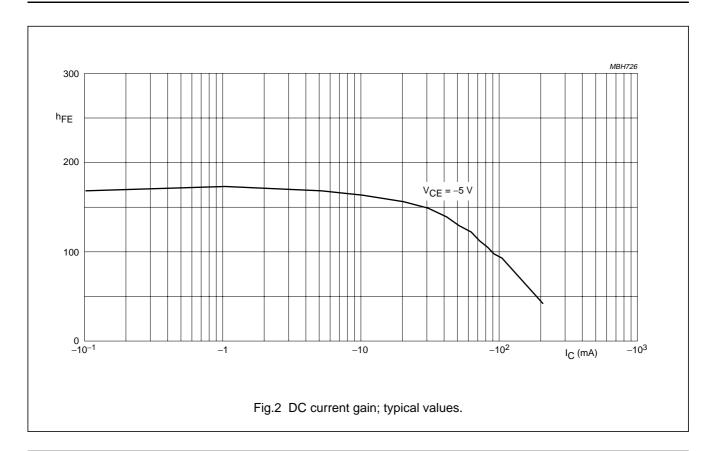
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = -30 V	_	-50	nA
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	-50	nA
h _{FE}	DC current gain	V _{CE} = −1 V; (see Fig.2)			
		$I_{\rm C} = -0.1 \text{mA}$	60	_	
		$I_C = -1 \text{ mA}$	80	_	
		$I_{\rm C} = -10 {\rm mA}$	100	300	
		I _C = -50 mA; note 1	60	_	
		$I_C = -100 \text{ mA}$; note 1	30	_	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	_	-250	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	-400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	_	-850	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	-950	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -5 \text{ V}$; $f = 100 \text{ MHz}$	_	4.5	pF
C _e	emitter capacitance	$I_C = I_C = 0$; $VE_B = -0.5 \text{ V}$; $f = 100 \text{ MHz}$	_	12	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -20 \text{ V};$ f = 100 MHz	150	_	MHz
F	noise figure	$I_C = -100 \mu A$; $V_{CE} = -5 V$; $R_S = 1 kΩ$; $f = 10 Hz$ to 15.7 kHz	_	4	dB
Switching	times (between 10% and 90% levels); (see Fig.3)			
t _{on}	turn-on time	$I_{Con} = -10 \text{ mA}; I_{Bon} = -1 \text{ mA};$	_	100	ns
t _d	delay time	I _{Boff} = 1 mA	_	50	ns
t _r	rise time		_	50	ns
t _{off}	turn-off time		_	700	ns
t _s	storage time		_	600	ns
t _f	fall time		_	100	ns

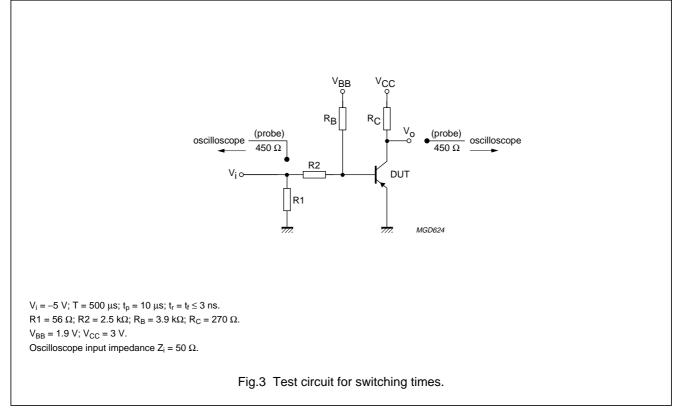
Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

PNP general purpose transistor

PMBS3906





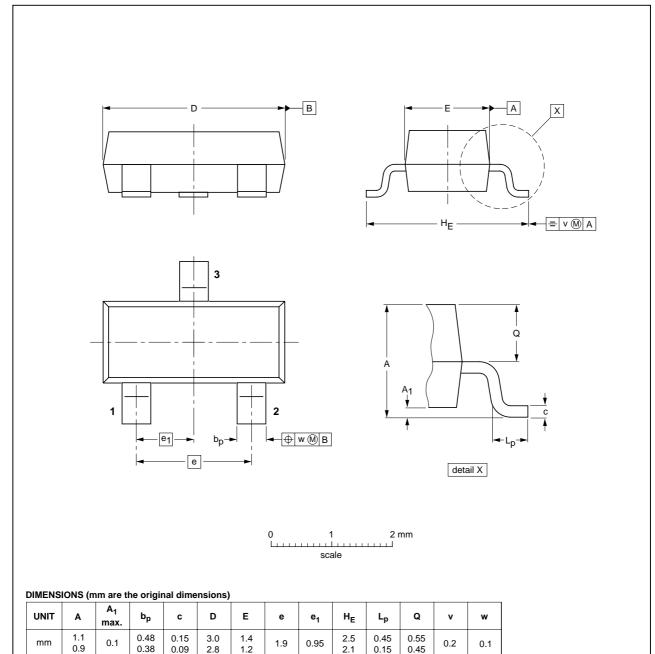
PNP general purpose transistor

PMBS3906

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



REFERENCES EUROPEAN			ISSUE DATE		
IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
	TO-236AB				-97-02-28- 99-09-13
	IEC	IEC JEDEC	IEC JEDEC EIAJ	IEC JEDEC EIAJ	IEC JEDEC EIAJ PROJECTION

PNP general purpose transistor

PMBS3906

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Printed in The Netherlands

R75/05/pp7

Date of release: 2004 Feb 02

Document order number: 9397 750 12456

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